

Patent Abstracts 1 Japan

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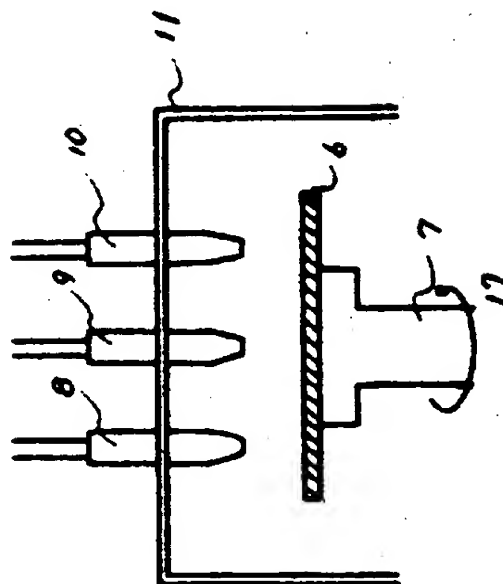
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TITLE : DEVELOPING METHOD



ABSTRACT : PURPOSE: To obtain a photoresist pattern with high precision and extremely high reproductivity and suitable for fine processing, by wetting the entire surface of a wafer with a surfactant, and dropping a developing soln. on it, and retaining it for a prescribed time on it.

CONSTITUTION: The wafer 6 is supported with a vacuum chuck, and a nonionic solvent diluted in water to the order of ppm is sprayed over the wafer 6 from the nozzle of a developing cup 11 so as to wet it throughout the entire surface, while the wafer 6 is rotated 17. A prescribed amt. of developing soln. is dropped from a developing nozzle 9. After developing it for a prescribed time, a rinse soln. is ejected from a rinse nozzle 10, and the surface of the wafer 6 is washed for a prescribed time while the wafer 6 is rotated. Then, the wafer 6 is rotated to dry it by blowing gaseous nitrogen or hot air on the wafer. As a result, development of extremely excellent in reproductivity and high in precision can be carried out.

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